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(71) Applicant *(for all designated States except US)*: **LAM RESEARCH CORPORATION** [US/US]; 4650 Cushing Parkway, Fremont, CA 94538 (US).

(72) Inventors; and
(75) Inventors/Applicants *(for US only)*: **HALSEY, Harlan, I.** [US/US]; 200 La Questa Way, Woodside, CA 94062 (US). **JACOB, David, E.** [US/US]; 40266 Pacific Street, Fremont, CA 94538 (US).

(74) Agent: **GENCARELLA, Michael, L.**; Martine & Penilla, LLP, Suite 170, 710 Lakeway Drive, Sunnyvale, CA 94085 (US).

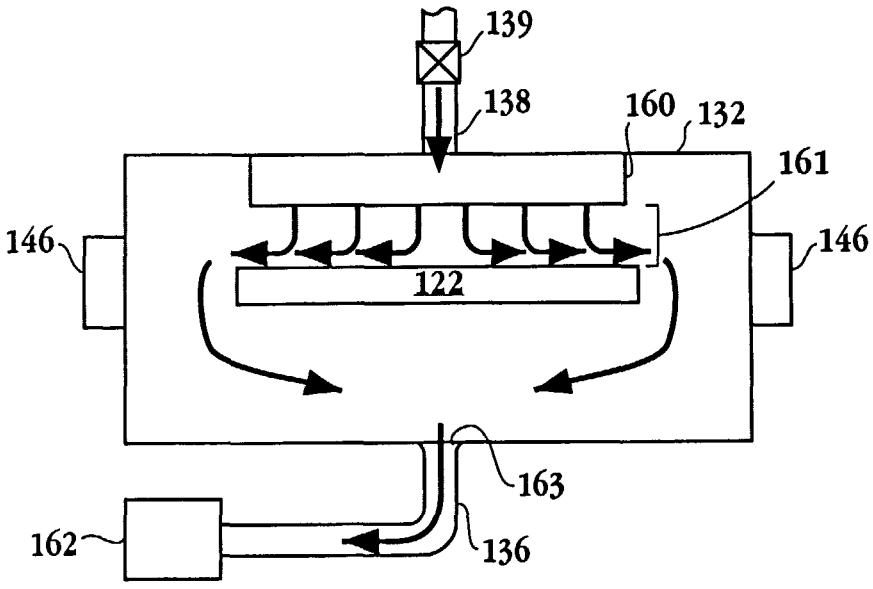
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(54) Title: RAPID CYCLE CHAMBER HAVING A TOP VENT WITH NITROGEN PURGE



(57) Abstract: A chamber (132) for transitioning a semiconductor substrate between modules operating at different pressures is provided. The chamber includes a base defining an outlet (136). The outlet permits removal of an atmosphere within the chamber to create a vacuum. A substrate support for supporting a semiconductor substrate (122) within the chamber is included. A chamber top having an inlet (138) is included. The inlet is configured to allow for the introduction of a gas into the chamber to displace moisture in a region defined above the substrate support. Sidewalls extending from the base to the chamber top are included. The sidewalls include access ports (146) for entry and exit of a semiconductor substrate from the chamber. A method for conditioning an environment above a region of a semiconductor substrate within a pressure varying interface is also provided.

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